

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method for improving uniformity of a film in a plasma enhanced chemical vapor deposition system in a deposition chamber, said method comprising, before a deposition procedure, steps of:

performing a cleaning procedure to remove particles adhered onto an internal wall of said deposition chamber;

performing a pre-deposition procedure to isolate contaminants generated during said cleaning procedure; and

introducing a specified ~~nonreactive~~ gas into said deposition chamber ~~for diluting contaminants to dilute and lower contaminant concentration~~ in said deposition chamber after said pre-deposition procedure so as to stabilize a condition inside said deposition chamber.

2. (Original) The method according to claim 1 wherein said contaminants include fluoride.

3. (Currently Amended) The method according to claim 1 wherein said specified ~~nonreactive~~ gas comprises at least a nitrogen gas.

4. (Currently Amended) The method according to claim 1 wherein said specified ~~nonreactive~~ gas comprises at least an argon gas.

5. (Currently Amended) The method according to claim 1 wherein said specified ~~nonreactive~~ gas comprises at least a hydrogen gas.

6. (Original) The method according to claim 1 wherein said condition to be stabilized is the temperature distribution condition in said deposition chamber.

7. (Original) The method according to claim 1 wherein said condition to be stabilized is the contaminant concentration in said deposition chamber.

8. (Original) The method according to claim 1 wherein said cleaning procedure is performed by introducing a nitrogen fluoride gas into said deposition chamber.

9. (Original) The method according to claim 1 wherein said pre-deposition procedure is performed by introducing a reaction gas without placing any substrate into said deposition chamber.

10. (Original) The method according to claim 1 further comprising a step of idling said deposition chamber for a specified period of time for stabilizing temperature distribution in said deposition chamber.

11-15. (Cancelled)

16. (Previously Presented) The method according to claim 10 wherein said specified period of time is ranged from 1 minute to 20 minutes.

17-21. (Cancelled)